

**Effect of radial energy distribution on ion track etching in amorphous metallic Fe<sub>81</sub>B<sub>13.5</sub>Si<sub>3.5</sub>C<sub>2</sub>**

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The influence of the radial energy distribution on the formation of ion tracks is investigated by track etching in amorphous metallic Fe<sub>81</sub>B<sub>13.5</sub>Si<sub>3.5</sub>C<sub>2</sub>. An etching threshold of almost 4 keV/Å is observed for high energy ions (Au, 35 MeV/u), which is slightly higher than the threshold of 3.6 keV/Å of low energy ions (Xe, 6.1 MeV/u). In the frame of the thermal-spike model, the track radius is calculated as a function of the ion energy loss. For a given energy loss, the model predicts a small increase of the etching threshold as a function of the ion energy, in agreement with the experimental results.